

P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a	Q _g (Typ.)			
60	0.225 at V _{GS} = - 10 V	- 3.0	00 =0			
- 60	0.315 at V _{GS} = - 4.5 V	- 0.9	23 nC			

FEATURES

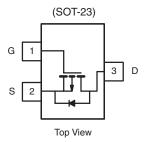
- DT-Trench Power MOSFET
- 100 % R_g Tested

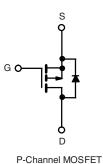
APPLICATIONS

- · Load Switch
- DC/DC Converter









Parameter	Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 60	V
Gate-Source Voltage		V _{GS}	± 20	V
	T _C = 25 °C		- 3.0	
Continuous Drain Current /T 150 °C)	T _C = 70 °C	1 ,	- 2.0	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	l _D	- 1.8 ^{b, c}	
	T _A = 70 °C		- 1.0 ^{b, c}	Α
Pulsed Drain Current		I _{DM}	- 9	
Continuos Courses Dunin Diada Current	T _C = 25 °C		- 3.0	
Continous Source-Drain Diode Current	T _A = 25 °C	I _S	- 1.2 ^{b, c}	
	T _C = 25 °C		1.2	
Marian In Danier Discipation	T _C = 70 °C		0.8	w
Maximum Power Dissipation	T _A = 25 °C	P _D	0.65 ^{b, c}	VV
	T _A = 70 °C		0.4 ^{b, c}	
Operating Junction and Storage Temperature	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Typical	Maximum	Unit			
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	85	110	°C/W			
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	45	55	C/VV			

Notes:

- a. Based on T_C = 25 °C.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. Maximum under steady state conditions is 166 $^{\circ}\text{C/W}.$

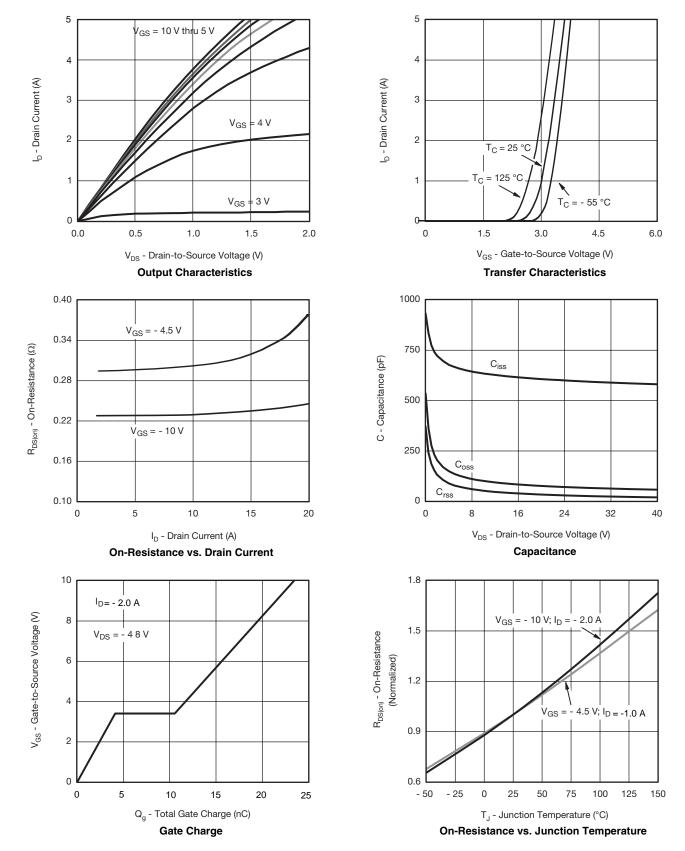


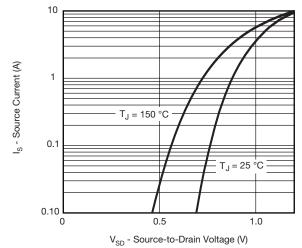
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 40		m\//°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	T _J I _D = - 250 μΑ		4.8		mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_{D} = -250 \mu A$	- 2.0		- 4.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 48 V, V _{GS} = 0 V			- 1	
		$V_{DS} = -48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$			- 5	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 3.0			Α
Drain Course On State Resistance	D	V _{GS} = - 10 V, I _D = - 2.0 A		225	280	
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	V _{GS} = - 4.5 V, I _D = - 1.0 A		315	390	Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 48 V, I _D = - 2.0 A		10		S
Dynamic ^b						
Input Capacitance	C _{iss}	C _{iss}		609		
Output Capacitance	C _{oss}	V _{DS} = - 48 V, V _{GS} = 0 V, f = 1 MHz		112		pF
Reverse Transfer Capacitance	C _{rss}	1 1		68		
Tatal Oats Observe	Qg	V _{DS} = -48 V, V _{GS} = -10 V, I _D = -2.0 A		23		nC
Total Gate Charge				12		
Gate-Source Charge	Q_{gs}	$V_{DS} = -48 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -1.0 \text{ A}$		2.5		
Gate-Drain Charge	Q_{gd}]		3.2		
Gate Resistance	R_g	f = 1 MHz		4.3		Ω
Turn-On Delay Time	t _{d(on)}			18		
Rise Time	t _r	$V_{DD} = -48 \text{ V}, R_L = 8 \Omega$		10		- - -
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1.0 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		41		
Fall Time	t _f]		13		
Turn-On Delay Time	t _{d(on)}			10		ns
Rise Time	t _r	$V_{DD} = -48 \text{ V}, R_{L} = 8 \Omega$		6		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 2.0 A, V_{GEN} = - 10 V, R_g = 1 Ω		33		
Fall Time	t _f	1		9		1
Drain-Source Body Diode Characteristic	s					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 3.0	۸
Pulse Diode Forward Current	I _{SM}				- 9	- A
Body Diode Voltage	V_{SD}	I _S = - 2.0 A, V _{GS} = 0 V		- 0.9	- 1.5	V
Body Diode Reverse Recovery Time	t _{rr}			25		ns
Body Diode Reverse Recovery Charge		1 00 A dl/dt 100 A / = T 05 00		32		nC
Reverse Recovery Fall Time	t _a	$I_F = -2.0 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		10		ns
Reverse Recovery Rise Time	t _b	1		7		

Notes:

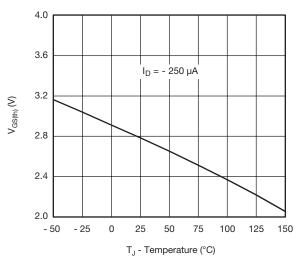
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

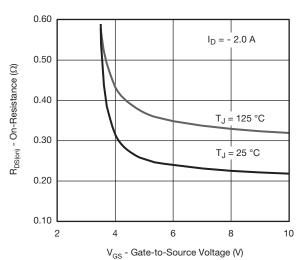




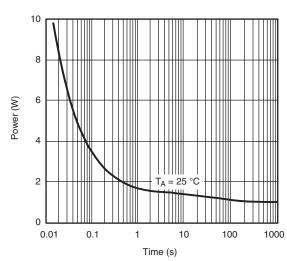
Source-Drain Diode Forward Voltage



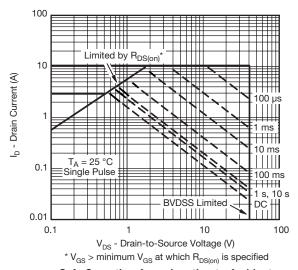
Threshold Voltage

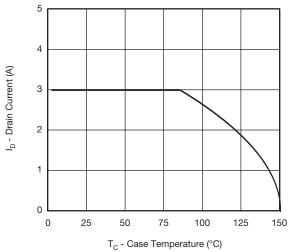


On-Resistance vs. Gate-to-Source Voltage

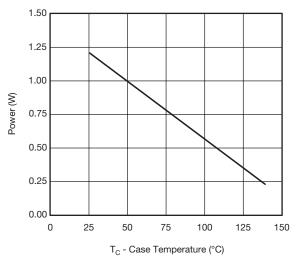


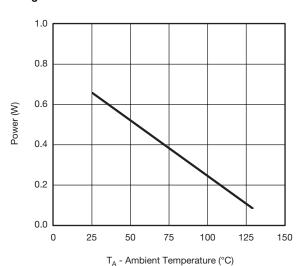
Single Pulse Power (Junction-to-Ambient)





Current Derating*

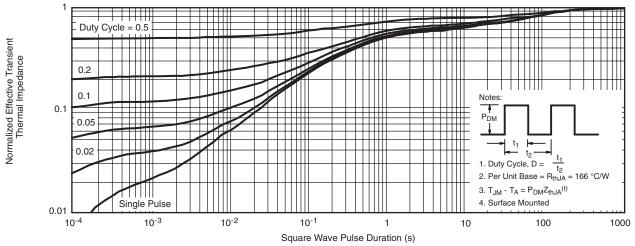




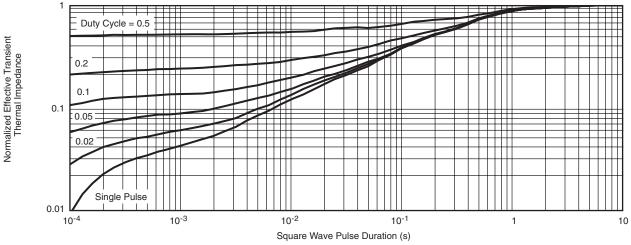
Power, Junction-to-Foot

Power, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



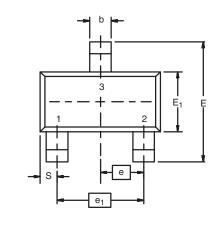
Normalized Thermal Transient Impedance, Junction-to-Ambient

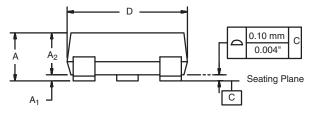


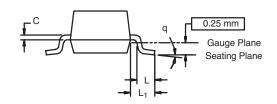
Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







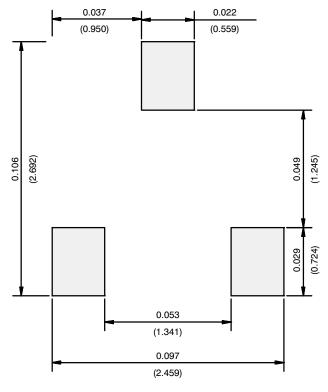
Dim	MILLIMETERS		INCHES			
	Min	Max	Min	Max		
Α	0.89	1.12	0.035	0.044		
A ₁	0.01	0.10	0.0004	0.004		
A ₂	0.88	1.02	0.0346	0.040		
b	0.35	0.50	0.014	0.020		
С	0.085	0.18	0.003	0.007		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E ₁	1.20	1.40	0.047	0.055		
е	0.95 BSC		0.037	0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref			
L	0.40	0.60	0.016	0.024		
L ₁	0.64 Ref		0.025	0.025 Ref		
S	0.50 Ref		0.020 Ref			
q	3°	8°	3°	8°		

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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